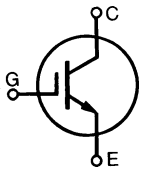
IXYS

HiPerFAST™ IGBT

	V_{CES}	$I_{C(25)}$	$V_{CE(sat)}$	t_{fi}
IXGH24N50B	500 V	48 A	2.3 V	80 ns
IXGH24N60B	600 V	48 A	2.5 V	80 ns

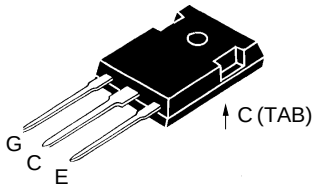
Preliminary data



Symbol	Test Conditions	Maximum Ratings		
		24N50	24N60	
V_{CES}	T_J = 25°C to 150°C	500	600	V
V_{CGR}	T_J = 25°C to 150°C; R_{GE} = 1 MΩ	500	600	V
V_{GES}	Continuous		±20	V
V_{GEM}	Transient		±30	V
I_{C25}	T_C = 25°C		48	A
I_{C90}	T_C = 90°C		24	A
I_{CM}	T_C = 25°C, 1 ms		96	A
SSOA (RBSOA)	V_{GE} = 15 V, T_{VJ} = 125°C, R_G = 22 Ω Clamped inductive load, L = 100 µH		I_{CM} = 48 @ 0.8 V_{CES}	A
P_C	T_C = 25°C		150	W
T_J			-55 ... +150	°C
T_{JM}			150	°C
T_{stg}			-55 ... +150	°C
Maximum lead temperature for soldering 1.6 mm (0.062 in.) from case for 10 s			300	°C
M_d	Mounting torque (M3)		1.13/10	Nm/lb.in.
Weight			6	g

Symbol	Test Conditions		Characteristic Values (T_J = 25°C, unless otherwise specified)			
			min.	typ.	max.	
BV_{CES}	I_C = 250 µA, V_{GE} = 0 V	24N50	500			V
		24N60	600			V
$V_{GE(th)}$	I_C = 250 µA, V_{CE} = V_{GE}		2.5		5	V
I_{CES}	V_{CE} = 0.8 • V_{CES}	T_J = 25°C			200	µA
	V_{GE} = 0 V	T_J = 125°C			1	mA
I_{GES}	V_{CE} = 0 V, V_{GE} = ±20 V				±100	nA
$V_{CE(sat)}$	I_C = I_{C90}, V_{GE} = 15 V	24N50			2.3	V
		24N60			2.5	V

TO-247 AD



G = Gate, C = Collector,
E = Emitter, TAB = Collector

Features

- International standard packages JEDEC TO-247 AD
- High frequency IGBT
- High current handling capability
- 3rd generation HDMOS™ process
- MOS Gate turn-on
  - drive simplicity

Applications

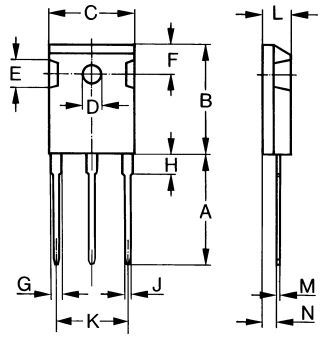
- AC motor speed control
- DC servo and robot drives
- DC choppers
- Uninterruptible power supplies (UPS)
- Switched-mode and resonant-mode power supplies

Advantages

- High power density
- Switching speed for high frequency applications
- Easy to mount with 1 screw (insulated mounting screw hole)

Symbol	Test Conditions		Characteristic Values (T_J = 25°C, unless otherwise specified) min.	typ.	max.	
g_{fs}	$I_C = I_{C90}$; V_{CE} = 10 V, Pulse test, t ≤ 300 µs, duty cycle ≤ 2 %		9	13		S
C_{ies}	V_{CE} = 25 V, V_{GE} = 0 V, f = 1 MHz			1500		pF
C_{oes}				135		pF
C_{res}				40		pF
Q_g	$I_C = I_{C90}$, V_{GE} = 15 V, V_{CE} = 0.5 V_{CES}			90	120	nC
Q_{ge}				11	15	nC
Q_{gc}				30	40	nC
$t_{d(on)}$	**Inductive load, T_J = 25°C**			25		ns
t_{ri}	$I_C = I_{C90}$, V_{GE} = 15 V, L = 100 µH,			15		ns
E_{on}	V_{CE} = 0.8 V_{CES}, $R_G = R_{off}$ = 10 Ω			0.6		mJ
$t_{d(off)}$	Remarks: Switching times may			150	200	ns
t_{fi}	increase for V_{CE} (Clamp) > 0.8 • V_{CES},			80	150	ns
E_{off}	higher T_J or increased R_G	24N50B		0.62		mJ
		24N60B		0.80		mJ
$t_{d(on)}$	**Inductive load, T_J = 125°C**			25		ns
t_{ri}	$I_C = I_{C90}$, V_{GE} = 15 V, L = 100 µH			15		ns
E_{on}	V_{CE} = 0.8 V_{CES}, $R_G = R_{off}$ = 10 Ω			0.8		mJ
$t_{d(off)}$	Remarks: Switching times may			250		ns
t_{fi}	increase for V_{CE} (Clamp) > 0.8 • V_{CES},			100		ns
E_{off}	higher T_J or increased R_G	24N50B		0.9		mJ
		24N60B		1.4		mJ
R_{thJC}					0.83	K/W
R_{thCK}				0.25		K/W

TO-247 AD (IXGH) Outline



Dim.	Millimeter Min.	Max.	Inches Min.	Max.
A	19.81	20.32	0.780	0.800
B	20.80	21.46	0.819	0.845
C	15.75	16.26	0.610	0.640
D	3.55	3.65	0.140	0.144
E	4.32	5.49	0.170	0.216
F	5.4	6.2	0.212	0.244
G	1.65	2.13	0.065	0.084
H	-	4.5	-	0.177
J	1.0	1.4	0.040	0.055
K	10.8	11.0	0.426	0.433
L	4.7	5.3	0.185	0.209
M	0.4	0.8	0.016	0.031
N	1.5	2.49	0.087	0.102

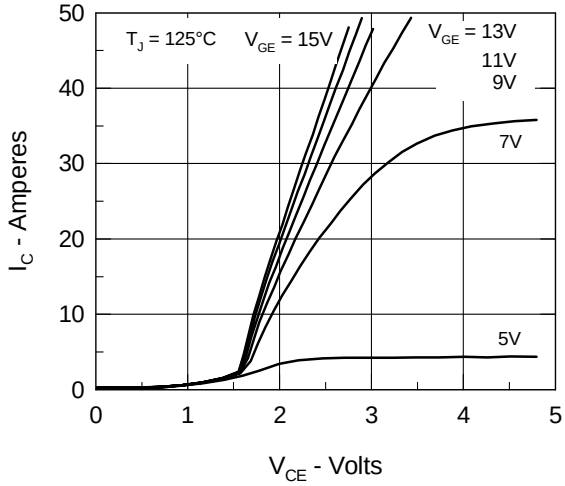


Fig. 1. Saturation Voltage Characteristics

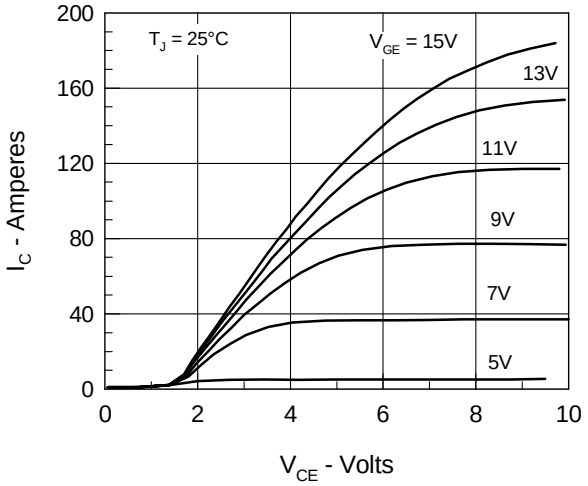


Fig. 2. Extended Output Characteristics

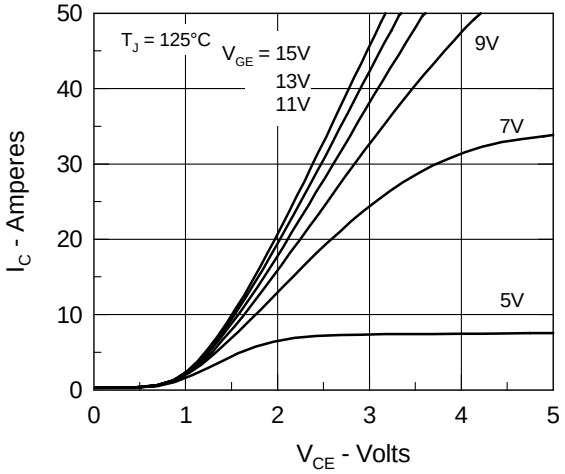


Fig. 3. Saturation Voltage Characteristics

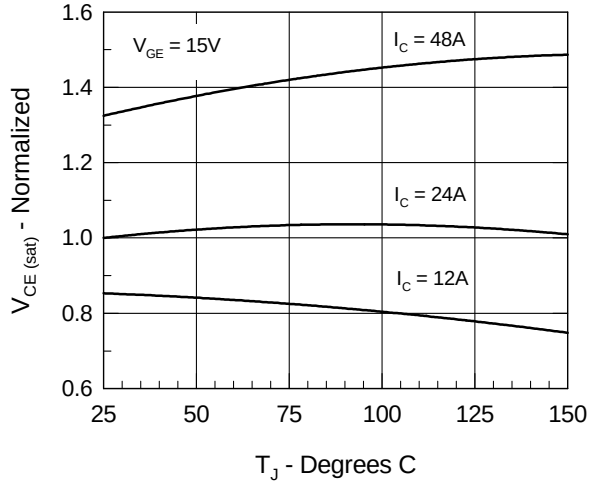


Fig. 4. Temperature Dependence of $V_{CE(sat)}$

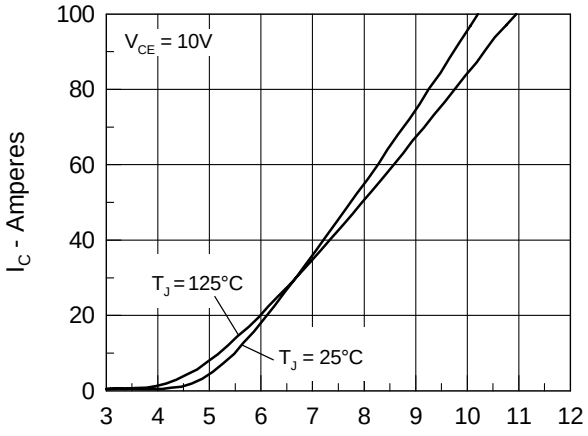


Fig. 5. Admittance Curves

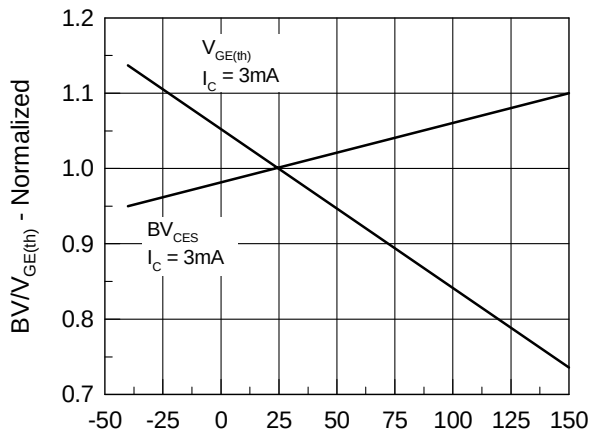


Fig. 6. Temperature Dependence of BV_{DSS} & $V_{GE(th)}$

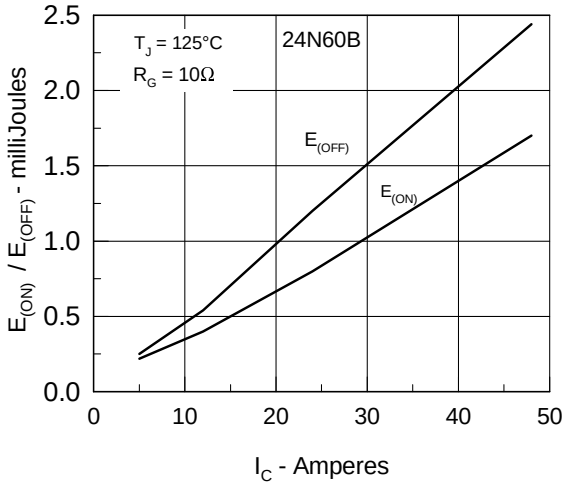


Fig. 7. Dependence of tfi and E_{OFF} on I_C.

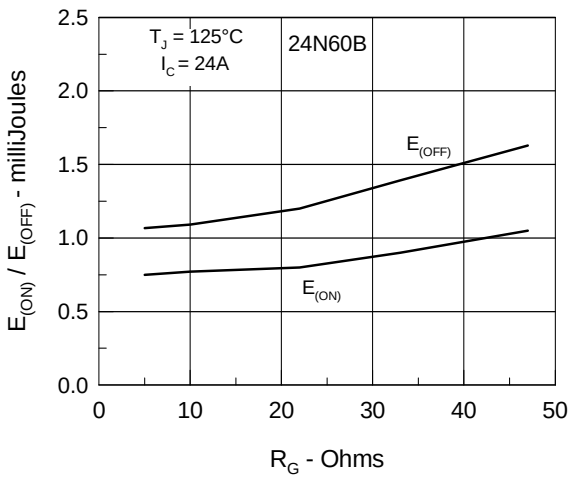


Fig. 8. Dependence of tfi and E_{OFF} on R_G.

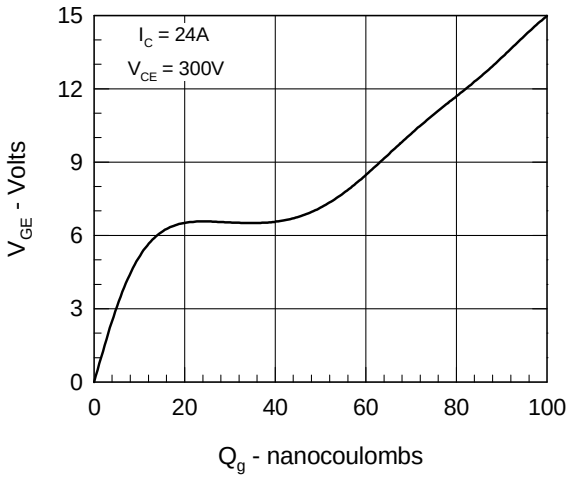


Fig. 9. Gate Charge

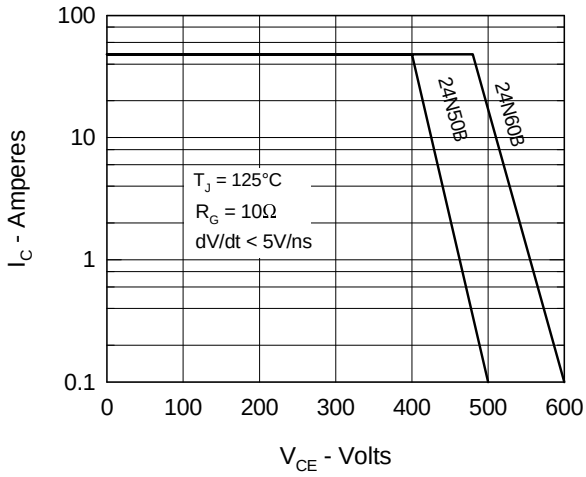


Fig. 10. Turn-off Safe Operating Area

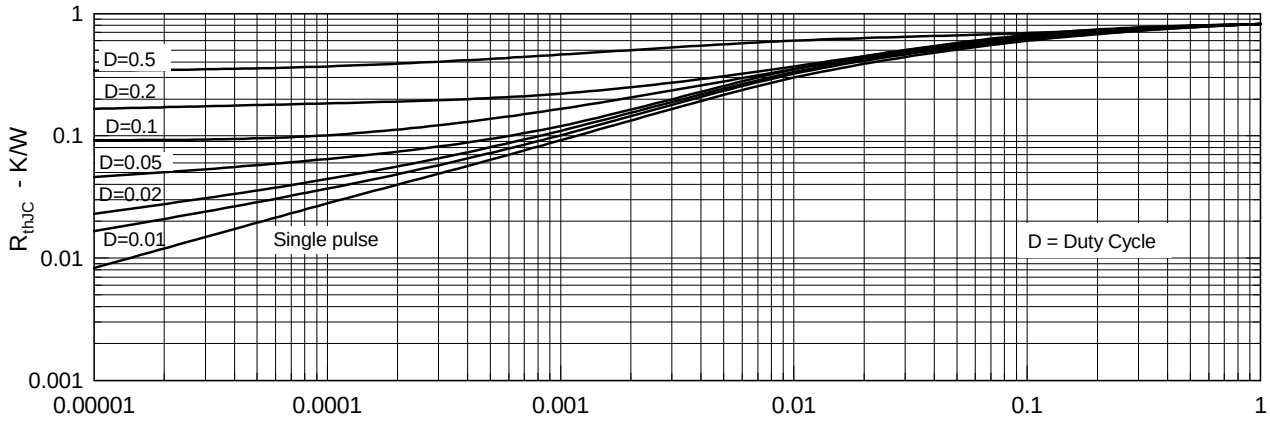


Fig. 11. Transient Thermal Resistance